Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- · 3Q technology for improved noise immunity
- High blocking voltage capability
- · High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- · Less sensitive gate for very high noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- · Triggering in three quadrants only

3. Applications

- Heating controls
- High power motor control
- · High power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 91 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	-	25	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	190	Α
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	-	209	А
T _j	junction temperature		-	-	125	°C
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	18	50	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	34	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>	-	1,3	1.55	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 25 A; dV_{com}/dt = 20 V/ μ s; gate open circuit; Fig. 12	-	44	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		T2—T1
3	G	gate		G sym051
mb	T2	mounting base; main terminal 2	1 3 TO-263 (D2PAK) E N	symoon

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA225B-600B	TO263	BTA225B-600B,118	Reel	800	TO263E (E)	26-May-2017
					TO263N (N)	26-Sep-2016

7. Marking

Table 4. Marking codes

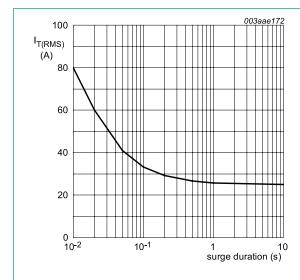
Type number	Marking codes			
	Assembly factory: E	Assembly factory: N		
BTA225B-600B	BTA225B 600B PJExxxx xx	BTA225B 600B PJNxxxx xx		

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 91 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	25	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	-	190	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 ms$	-	209	Α
l ² t	I ² t for fusing	t _P = 10 ms; SIN	-	180	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 100 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C



f = 50 Hz; T_{mb} = 91 °C Fig. 1. RMS on-state current as a function of surge duration; maximum values

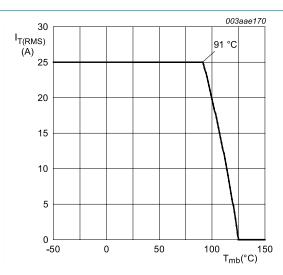
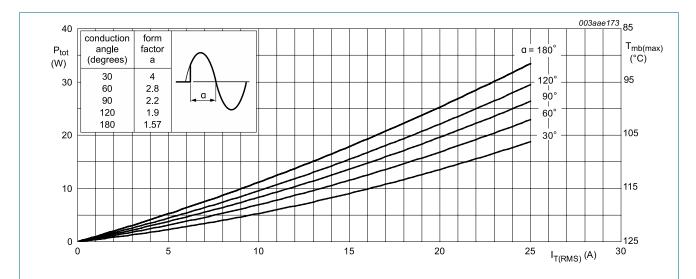
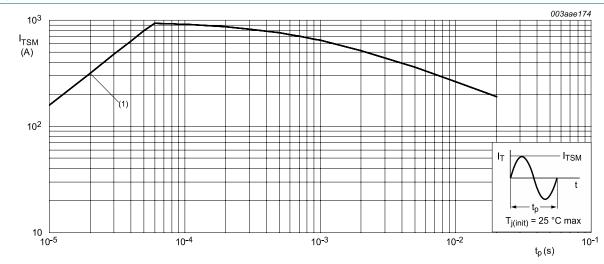


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 α = conduction angle

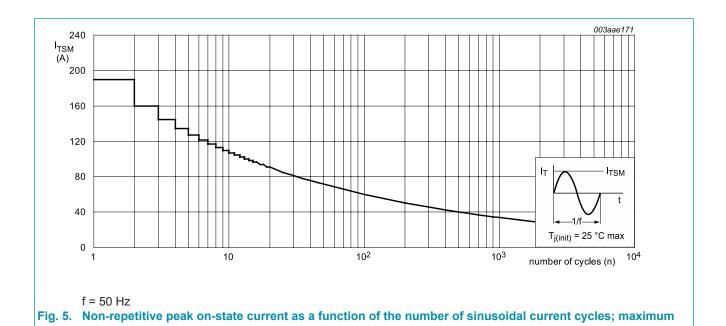
 $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$ Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



t_p ≤ 20 ms

(1) dl_⊤/dt limit

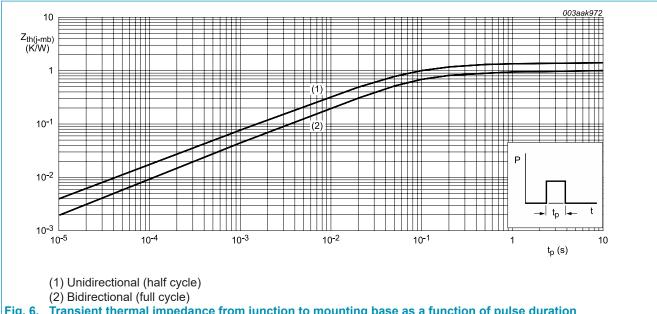
Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig. 6	-	-	1	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	1.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W

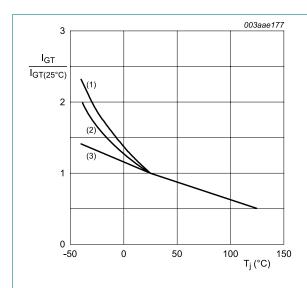


Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT} gate trigger current	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 °C; Fig. 7$	2	18	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; $ $T_j = 25 \text{ °C}; Fig. 7$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	2	34	50	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	-	31	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \text{Fig. 8}$	-	34	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{Fig. 8}$	-	30	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>	-	1,3	1.55	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics				'	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 25 A; dV_{com}/dt = 20 V/ μ s; gate open circuit; Fig. 12	-	44	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

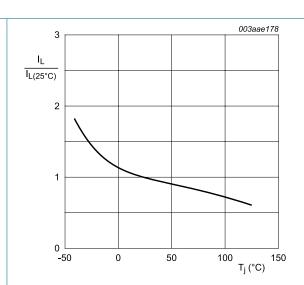


Fig. 8. Normalized holding current as a function of junction temperature

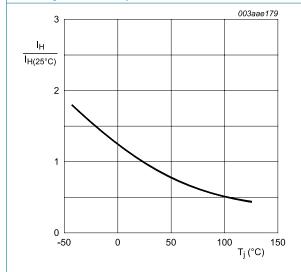
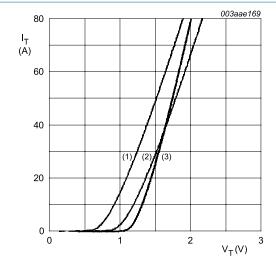
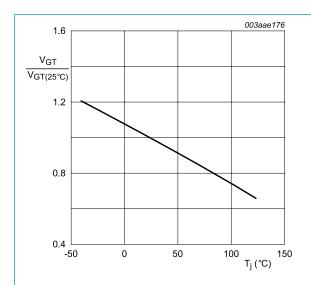


Fig. 9. Normalized holding current as a function of junction temperature



- V_o = 1.073 V; R_s = 0.015 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage





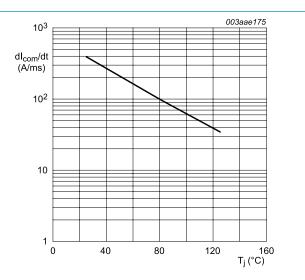
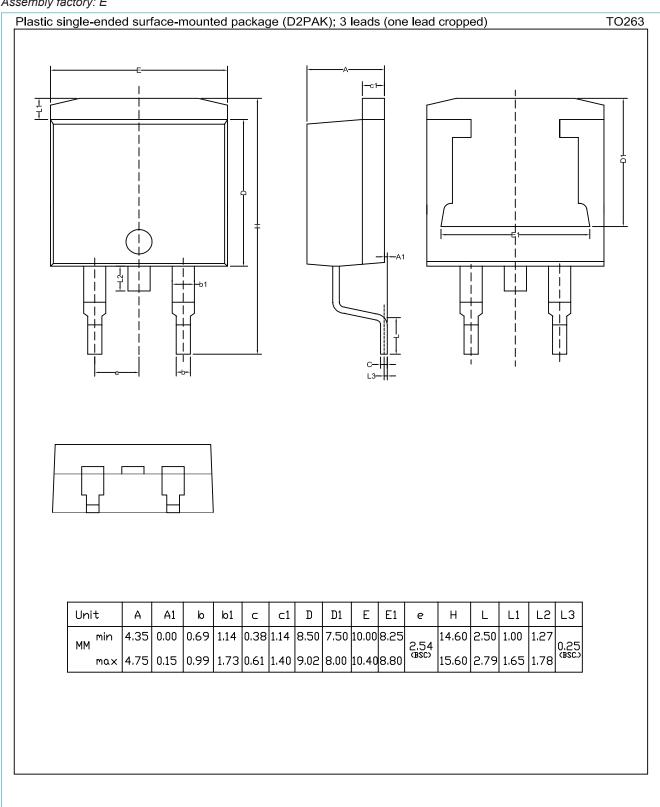


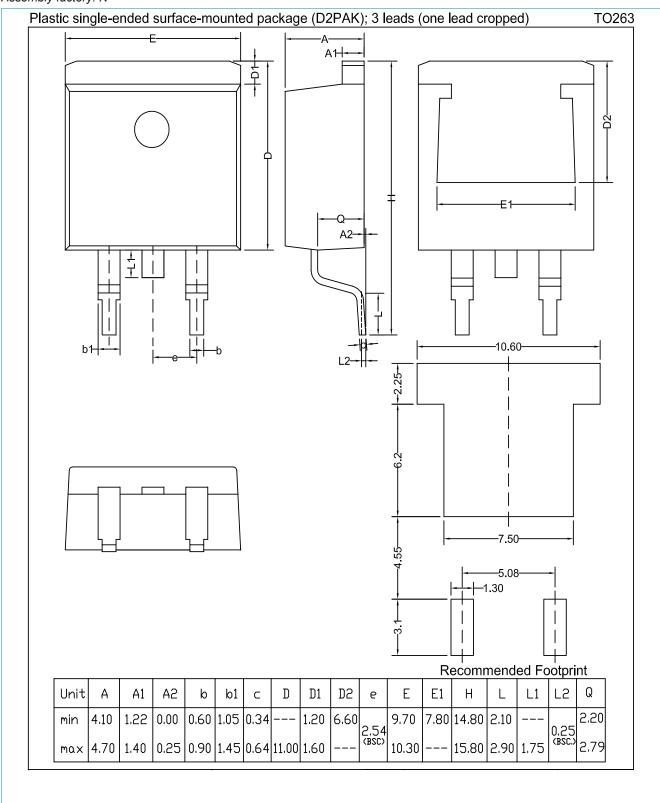
Fig. 12. Critical rate of change of commutating current as a function of junction temperature; typical values

11. Package outline

Assembly factory: E



Assembly factory: N



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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